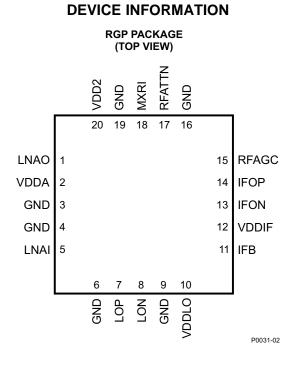


# 3.5-GHz, HIGH DYNAMIC RANGE, LOW-NOISE DOWN-CONVERTER

### **FEATURES**

- Performs First Down-Conversion in 3.5-GHz Radios (3300–3800 MHz)
- Integrated LNA/Mixer/IF Amp/LO Buffer
- Provision for External Image Reject/Band-Pass Filter
- Low Noise-Figure/High Linearity
- Digital 10-dB Attenuator for High-Level Signals
- Frequency Range: 3.3–3.8 GHz
- 28 dB of Gain with 20 dB of Gain Control (10-dB Fixed)
- 2.5-dB Noise Figure, Typical
- LO Drive Level = 0 dBm, Typical



## DESCRIPTION

The TRF1216 is the first of two integrated circuits used in the receiver section of Texas Instruments' 3.5-GHz radio chipset. The TRF1216 down-converts the 3.5-GHz input frequency to an intermediate frequency in the range of 400 MHz to 500 MHz. The device provides a differential output that passes through a SAW filter before connecting to a second down converter. For the best performance, Texas Instruments TRF1212 should be used to perform both the second down conversion and also provide the local oscillator for the TRF1216.

The TRF1216 includes a LNA with switchable attenuation, a balanced mixer, a variable gain IF amplifier and a differential LO Buffer for improved performance. In order to provide exceptional image rejection and extra jammer immunity, the TRF1216 offers a signal path to an off-chip filter. Specifications are provided assuming an in-band 2-dB insertion loss filter. To maximize input dynamic range, a 10-dB switchable attenuator is provided in the RF path as well as 10 dB of analog IF gain control. After the image reject filter, an on-chip Balun converts the signal from single ended to differential in order to provide better noise immunity at the mixer.



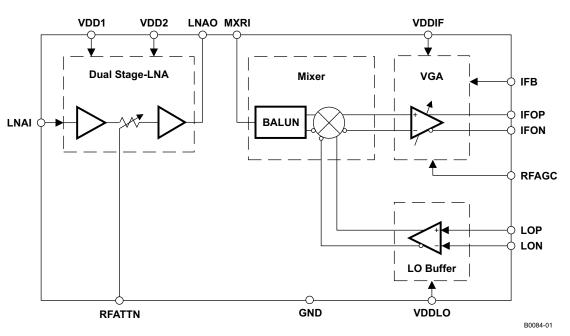
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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### **BLOCK DIAGRAM**

The detailed block diagram and the pin-out of the ASIC are shown in Figure 1 and Table 1.



TERMINAL		1/0	TVDE	DESCRIPTION				
NO.	NAME			DESCRIPTION				
1	LNAO	0	Analog	LNA Output, 50 Ω, ac-coupled				
2	VDD1	Ι	Power	LNA1 DC Bias (+5 V nominal)				
3, 4, 6, 9, 16, 19	GND	-	-	Ground				
5	LNAI	Ι	Analog	RF input – Needs dc block and input matching for optimum noise figure				
7	LOP	Ι	Analog	LO input positive, ac coupled				
8	LON	Ι	Analog	LO input negative, ac coupled				
10	VDDLO	Ι	Power	LO DC Bias (+5 V nominal)				
11	IFB	-	-	Not connected for normal operation. IF Bias Adjustment. Do not ground this pin or connect to any other pin.				
12	VDDIF	Ι	Power	IF Bias Network dc Bias (+5 V nominal)				
13	IFON	0	Analog	IF output and bias (see the application schematic for connections).				
14	IFOP	0	Analog	IF output and bias (see the application schematic for connections).				
15	RFAGC	I	Analog	Input voltage for analog gain control V <sub>RFAGC</sub> = 0 V to 1.5 V Max gain at V <sub>RFAGC</sub> = 0 V Min gain at V <sub>RFAGC</sub> = 1.5 V				
17	RFATTN	I	Digital	TTL control for switched attenuator TTL low – Attenuator switched in TTL high – Attenuator switched out				
18	MXRI	Ι	Analog	Mixer Input 50 Ω				
20	VDD2	-	Power	LNA2 dc bias (+5 V nominal)				
Back	GND	-	-	Back of package has metal base that must be grounded for thermal and RF performance.				

#### **TERMINAL FUNCTIONS**

#### **ABSOLUTE MAXIMUM RATINGS**

		VALUES	UNIT
V <sub>DD</sub>	DC supply voltage, VDD	0 to 5.5	V
P <sub>IN</sub>	RF input power	10	dBm
TJ	Junction temperature	200	°C
PD	Power dissipation	1100	mW
VD	Digital input voltage	–0.3 to 5.5	V
V <sub>A</sub>	Analog input voltage	–0.3 to 5	V
θ <sub>JC</sub>	Thermal resistance junction-to-case <sup>(1)</sup>	9.1	°C/W
T <sub>stg</sub>	Storage temperature	-40 to 105	°C
T <sub>op</sub>	Operating temperature	-40 to 85	°C
	Lead temperature (40 Sec Max)	260	°C

(1) Thermal resistance is junction to ambient assuming thermal pad with nine thermal vias under package metal base. See the recommended PCB layout.

### **ELECTRICAL CHARACTERISTICS**

The characteristics listed in the following tables are at V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C unless otherwise specified.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC CH	ARACTERISTICS		I			
$V_{DD}$	Supply voltage			5	5.5	V
I <sub>DD</sub>	Total supply current			175	200	mA
I <sub>LNA1</sub>	LNA1 supply current	Pin 2 (VDD1)		35		mA
I <sub>LNA2</sub>	LNA2 supply current	Pin 20 (VDD2)		35		mA
I <sub>IF</sub>	IF AMP supply current	Pin 12 (VDDIF) plus IF drain bias on pins 13 and 14 (IFOP, IFON)		55		mA
I <sub>LO</sub>	LO supply current	Pin 10 (VDDLO)		50		mA
V <sub>AGC</sub>	Gain control voltage		0		2	V
I <sub>AGC</sub>	Gain control current		0		100	μA
VIH	Input high voltage		2.5		5	V
V <sub>IL</sub>	Input low voltage		0		0.8	V
I <sub>IH</sub>	Input high current				300	μA
IIL	Input low current				-50	μA



## **DOWNCONVERTER CHARACTERISTICS**

Unless otherwise stated  $V^{}_{DD}$  = 5 V, FRF = 3500 MHz,  $T^{}_{A}$  = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
F <sub>RF</sub>	RF input frequency		3300		3800	MHz	
F <sub>LO</sub>	LO input frequency		2800		3400	MHz	
F <sub>IF</sub>	IF output frequency		400	480	500	MHz	
G	Maximum gain	$V_{AGC}$ = 0 V, RFATTN disabled, Measured into 100- $\Omega$ differential load	27	30	33	dB	
$\Delta_{\rm AGC}$	Analog gain control range	$V_{AGC}$ from 0 to 1.5 V, Any RFATTN setting. Measured into 100- $\Omega$ differential load	7	10		dB	
$\Delta_{\rm ATTN}$	Switched attenuator range	RFATTN from high-to-low, any VAGC setting. Measured into 100-Ω differential load	8.5	10	11.5	dB	
G <sub>HG</sub>	Gain flatness full band	Any 200-MHz band		1	2	dB	
G <sub>NB</sub>	Gain flatness / 6 MHz	Any 6-MHz band			0.4	dB	
NF		V <sub>AGC</sub> = 0 V, RFATTN disabled	2.5				
	Noise figure <sup>(1)</sup>	V <sub>AGC</sub> = 0 V, RFATTN enabled		4.8		٩D	
	Noise ligure (*)	V <sub>AGC</sub> = 1.5 V, RFATTN disabled	3.2			dB	
		V <sub>AGC</sub> = 1.5 V, RFATTN enabled		6.8			
		V <sub>AGC</sub> = 0 V, RFATTN disabled		-17			
IP-1dB	Input power at 1 dP compression	V <sub>AGC</sub> = 0 V, RFATTN enabled		-6		dBm	
IP-IUD	Input power at 1-dB compression	V <sub>AGC</sub> = 1.5 V, RFATTN disabled	-10			abm	
		V <sub>AGC</sub> = 1.5 V, RFATTN enabled		-4			
		V <sub>AGC</sub> = 0 V, RFATTN disabled		-7			
IIP3	Input 2rd order intercent point	V <sub>AGC</sub> = 0 V, RFATTN enabled		-1		ID	
115	Input 3rd order intercept point	$V_{AGC}$ = 1.5 V, RFATTN disabled		-5		dBm	
		V <sub>AGC</sub> = 1.5 V, RFATTN enabled	5				
P <sub>LO</sub>	LO input power	Referenced to $100-\Omega$ differential		0		dBm	
	LO to MXRI leakage	LO input = 3 dBm, V <sub>AGC</sub> = 0 V	-35	-45		dB	
	LO to IF leakage	LO input = 3 dBm, V <sub>AGC</sub> = 0 V	-40	-50		dB	
	LNAO to RXI isolation	F <sub>RF</sub> F = 3300 to 3800 MHz, RFATTN = TTL High	40			dB	

(1) Assured by lab characterization/design and not subject to production test.



### **TYPICAL CHARACTERISTICS**

Measurements resulting in the following graphs were taken on the evaluation board of the ASIC (see Figure 9).

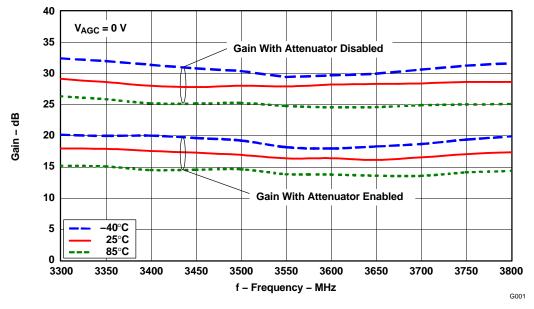


Figure 2. Gain vs Frequency for VAGC = 0 V

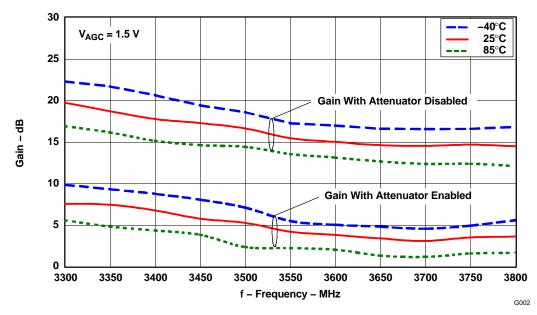
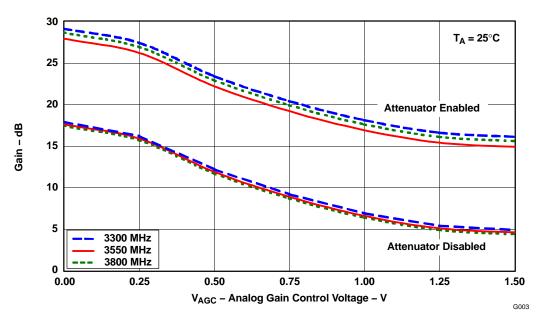
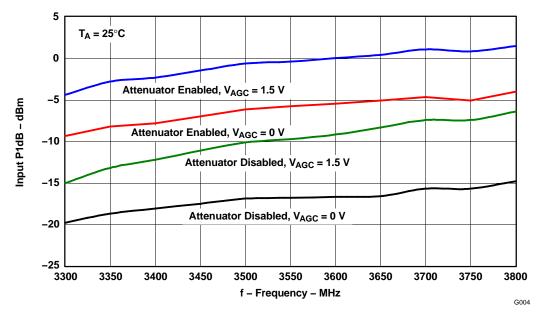


Figure 3. Gain vs Frequency for VAGC = 1.5 V



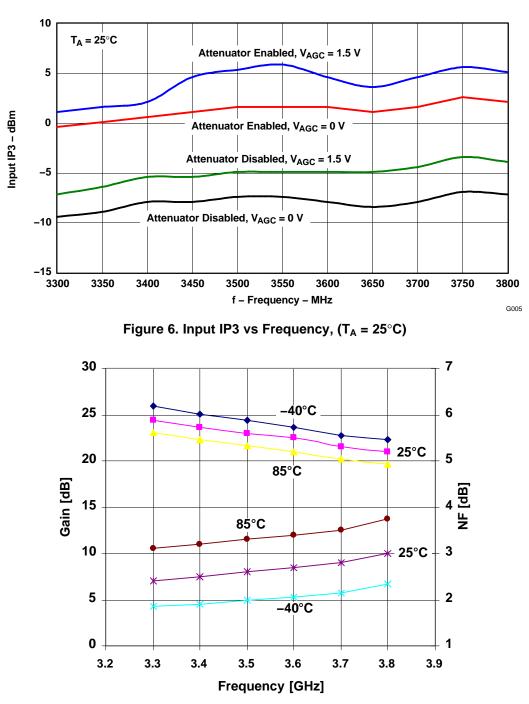












## **TYPICAL CHARACTERISTICS (continued)**

Figure 7. LNA Noise Figure vs Frequency With VAGC = 0 V

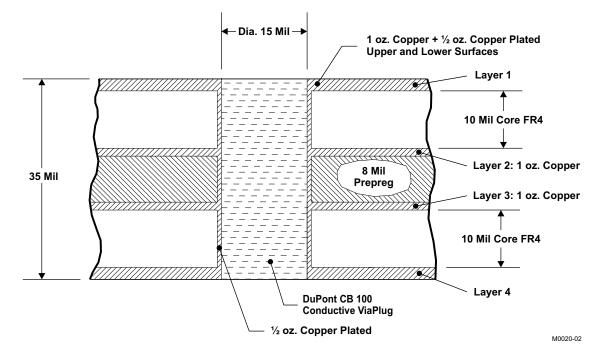
### **APPLICATION INFORMATION**

A typical application schematic is shown in Figure 9.

The PCB material recommendations are shown in Table 1 and Figure 8.

#### Table 1. PCB Recommendations

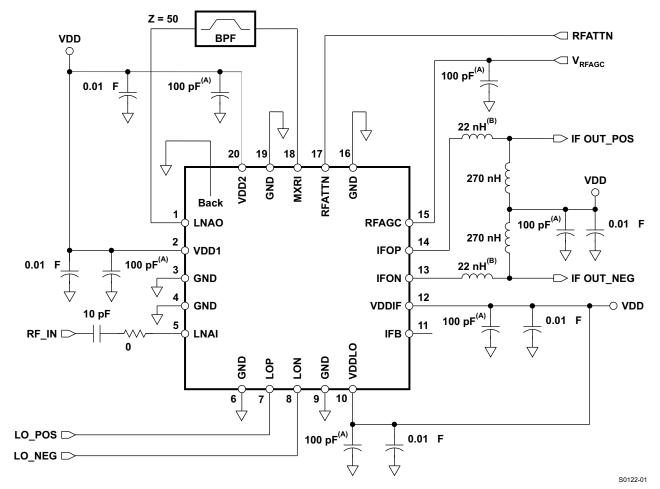
Board Material	FR4
Board Material Core Thickness	10 mil
Copper Thickness (starting)	1 oz
Prepreg Thickness	8 mil
Recommended Number of Layers	4
Via Plating Thickness	1/2 oz
Final Plate	White immersion tin
Final Board Thickness	33–37 mil



NOTE: Top and bottom surface finish: copper flash with 50–70  $\mu\textsc{in}$  white tin immersion.

Figure 8. PCB Construction and Via Cross Section

# TRF1216

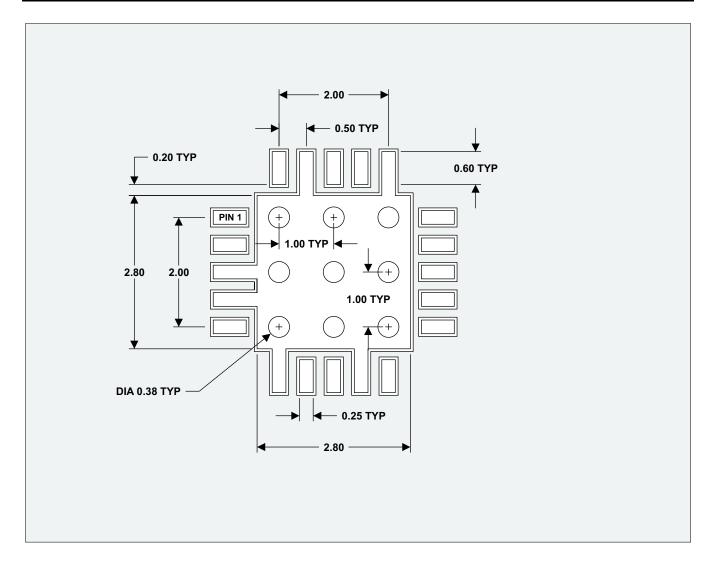


A. Place 100-pF capacitors close to package pins.

B. Place 22-nH inductors close to package pins.

#### Figure 9. Recommended Application Schematic





Solder Mask. No Solder Mask Under Chip, On Lead Pads or On Ground Connections.

Notes: 9 Via Holes, Each 0.38 mm. Dimensions in mm

### Figure 10. Recommended Pad Layout

M0022-02



31-Oct-2013

### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TRF1216IRGPR	ACTIVE	QFN	RGP	20	3000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	TRF 1216	Samples
TRF1216IRGPRG3	ACTIVE	QFN	RGP	20	3000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	TRF 1216	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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31-Oct-2013

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#### TAPE AND REEL INFORMATION





### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All di	mensions	are	nominal	

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TRF1216IRGPR	QFN	RGP	20	3000	330.0	12.4	4.3	4.3	1.5	8.0	12.0	Q2

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# PACKAGE MATERIALS INFORMATION

12-Aug-2013



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TRF1216IRGPR	QFN	RGP	20	3000	338.1	338.1	20.6

# **MECHANICAL DATA**



All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994. Α.

- Β. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.

D. The package thermal pad must be soldered to the board for thermal and mechanical performance.

- See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions. E.
- 🖄 Check thermal pad mechanical drawing in the product datasheet for nominal lead length dimensions.



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